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FDN308P

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

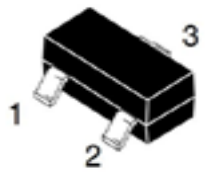
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

Applications

- Power management
- Load switch
- Battery protection

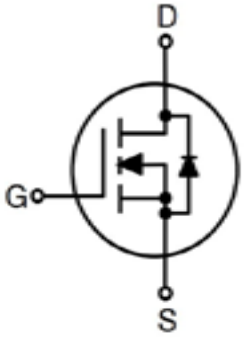
Features

- –20 V, –1.5 A. $R_{DS(ON)}$ = 125 mΩ @ V_{GS} = –4.5 V
  $R_{DS(ON)}$ = 190 mΩ @ V_{GS} = –2.5 V
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT™ -3 provides low $R_{DS(ON)}$ and 30% higher power handling capability than SOT23 in the same footprint



SOT-23

1 – Gate
2 – Source
3 – Drain



Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		–20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Drain Current – Continuous	(Note 1a)	–1.5	A
	– Pulsed		–10	
P_D	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

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Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = –250 μA	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		–13		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –16 V, V_{GS} = 0 V			–1	μA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = 12 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = –12 V V_{DS} = 0 V			–100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = –250 μA	–0.6	–1.0	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = –4.5 V, I_D = –1.5 A V_{GS} = –2.5 V, I_D = –1.3 A V_{GS} = –4.5 V, I_D = –1.5A T_J=125°C		86 136 114	125 190 178	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = –4.5 V, V_{DS} = –5 V	–5			A
g_{FS}	Forward Transconductance	V_{DS} = –5 V, I_D = –1.5 A		12		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –10 V, V_{GS} = 0 V, f = 1.0 MHz		341		pF
C_{oss}	Output Capacitance			83		pF
C_{rss}	Reverse Transfer Capacitance			43		pF
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = –10 V, I_D = –1 A, V_{GS} = –4.5 V, R_{GEN} = 6 Ω		8	16	ns
t_r	Turn–On Rise Time			10	20	ns
$t_{d(off)}$	Turn–Off Delay Time			12	22	ns
t_f	Turn–Off Fall Time			8	16	ns
Q_g	Total Gate Charge	V_{DS} = –10V, I_D = –1.5 A, V_{GS} = –4.5 V		3.8	5.4	nC
Q_{gs}	Gate–Source Charge			0.8		nC
Q_{gd}	Gate–Drain Charge			1.0		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–0.42	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = –0.42 (Note 2)		–0.7	–1.2	V

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Typical Characteristics

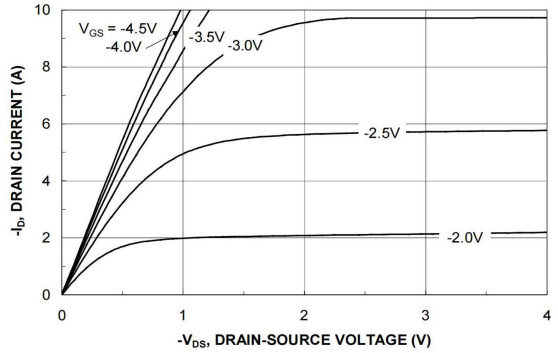


Figure 1. On-Region Characteristics.

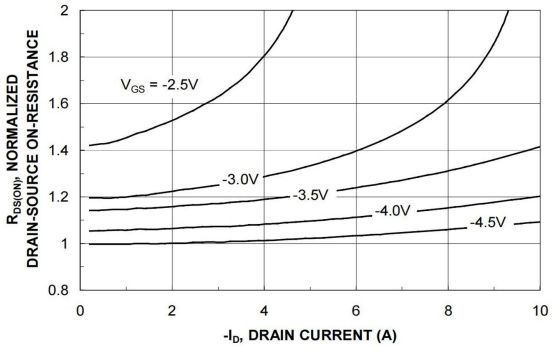


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

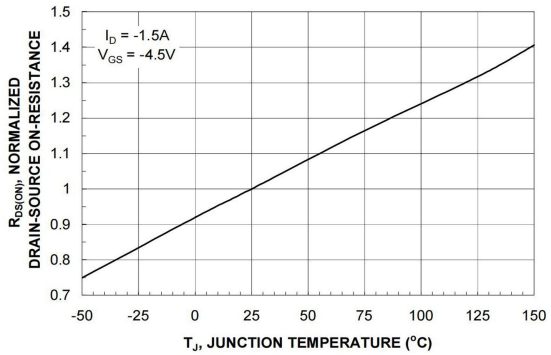


Figure 3. On-Resistance Variation withTemperature.

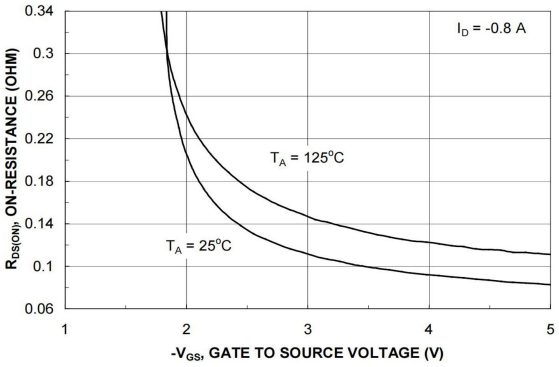


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

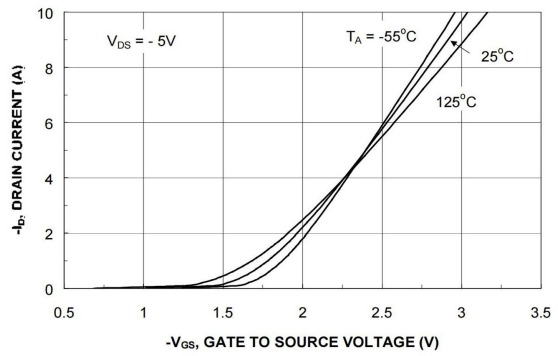


Figure 5. Transfer Characteristics.

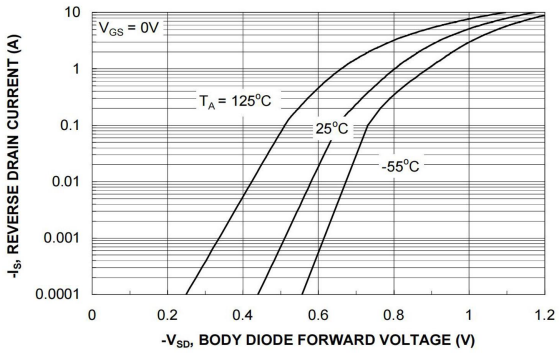


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

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Typical Characteristics

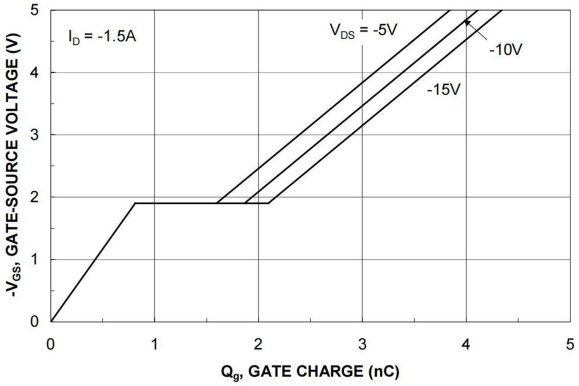


Figure 7. Gate Charge Characteristics.

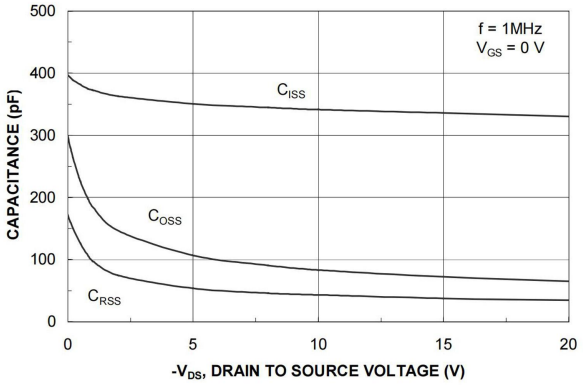


Figure 8. Capacitance Characteristics.

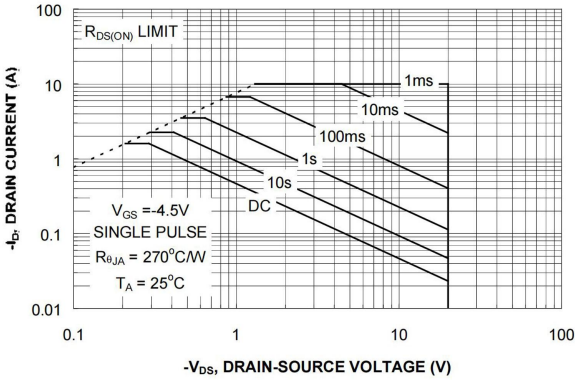


Figure 9. Maximum Safe Operating Area.

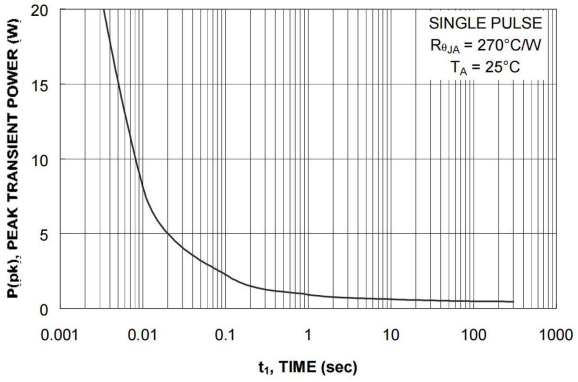
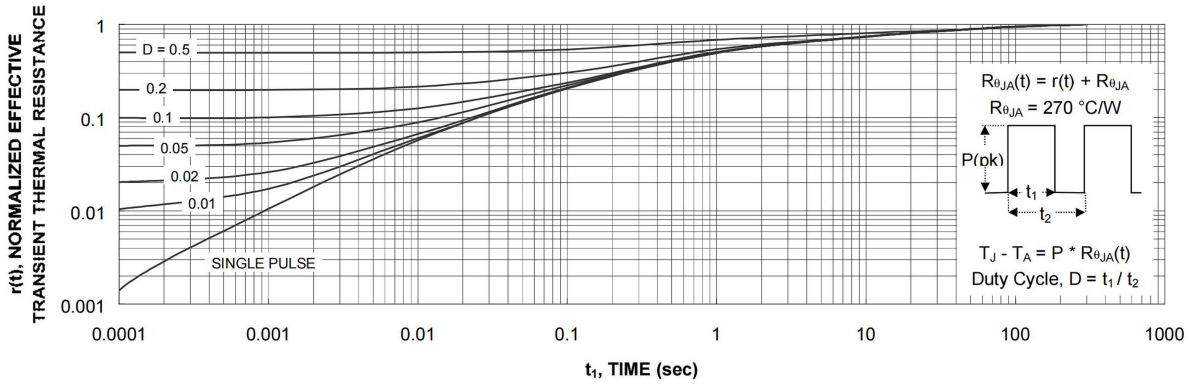


Figure 10. Single Pulse Maximum Power Dissipation.

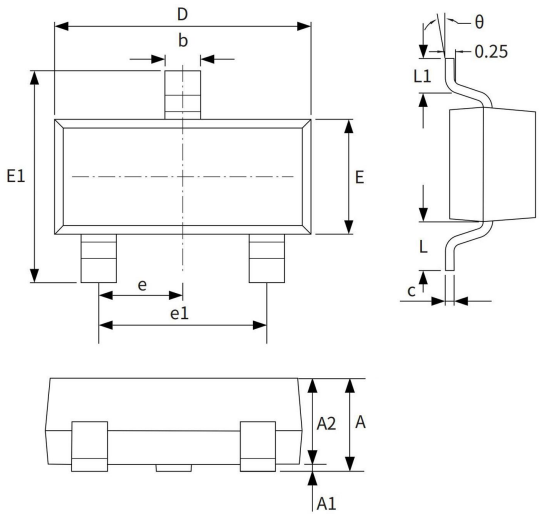


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Ordering Information

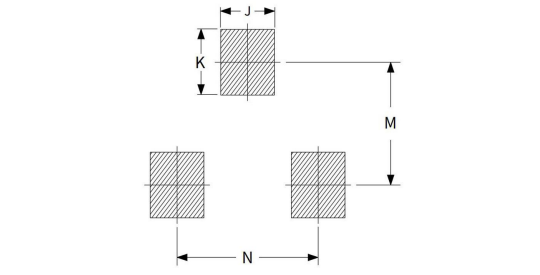
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077